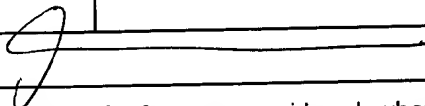


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Atty. Docket No. 04329.2222				Serial No. Not Yet Assigned			
Applicant Kouji MATSUO et al.							
Filing Date January 28, 2000				Group			
U.S. PATENT DOCUMENTS							
Examiner Initial*		Document Number	Date	Name	Class	Sub Class	Filing Date If Appropriate
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation Yes or No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
con		Wittner, M. et al. "Oxidation Kinetics of TiN Thin Films", J. Appl. Phys., Vol. 52, pp. 6659-6664, November (1981).					
sn		Matsuo, K. et al., "Reliable High-k TiO ₂ Gate Insulator Formed by Ultrathin TiN Deposition and Low Temperature Oxidation", Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials pp. 164-165, (1999).					
Examiner 				Date Considered 10/16/01			
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